

Features

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Product Summary

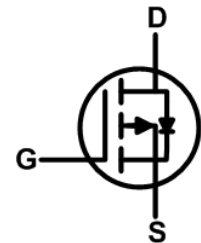
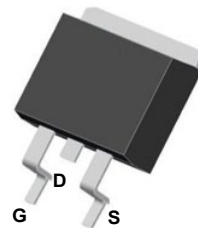


BVDSS	RDSON	ID
-100V	12mΩ	-120A

Applications

- Battery switching application
- Hard switched and high frequency circuits
- Power management

TO263Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	-120	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	-64	A
I_{DM}	Pulsed Drain Current ²	-600	A
EAS	Single Pulse Avalanche Energy ³	1458	mJ
I_{AS}	Avalanche Current	---	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	300	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	65	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.50	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-100	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =1mA	---	---	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-22A	---	12	15	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-2	-3	-4	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	---	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-100V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =-100V , V _{GS} =0V , T _J =100°C	---	---	---	
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V , V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-10V , I _D =-5A	---	---	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	---	---	Ω
Q _g	Total Gate Charge	V _{DS} =-50V , V _{GS} =-10V , I _D =-5A	---	136	---	nC
Q _{gs}	Gate-Source Charge		---	36	---	
Q _{gd}	Gate-Drain Charge		---	24.8	---	
T _{d(on)}	Turn-On Delay Time	V _{GS} =-10V , V _{DS} =-50V , I _D =-22A , R _G =1Ω	---	18	---	ns
T _r	Rise Time		---	43	---	
T _{d(off)}	Turn-Off Delay Time		---	125	---	
T _f	Fall Time		---	43	---	
C _{iss}	Input Capacitance	V _{DS} =-50V , V _{GS} =0V , f=1MHz	---	9349	---	pF
C _{oss}	Output Capacitance		---	798	---	
C _{rss}	Reverse Transfer Capacitance		---	111.2	---	

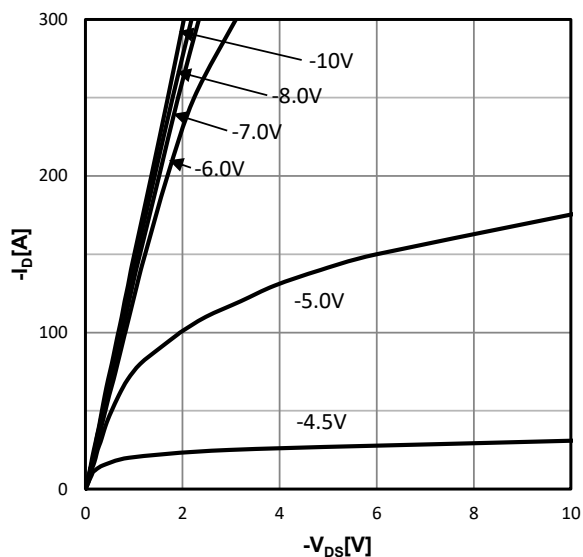
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V , Force Current	---	---	-120	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-20A , T _J =25°C	---	---	-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-20A , di/dt=100A/μs	---	107	---	nS
Q _{rr}	Reverse Recovery Charge	μs , T _J =25°C	---	216.8	---	nC

a1: Repetitive rating; pulse width limited by maximum junction temperature
a2: V_{DD}=-50V, L=1mH, R_G=25Ω, Starting T_J=25°C

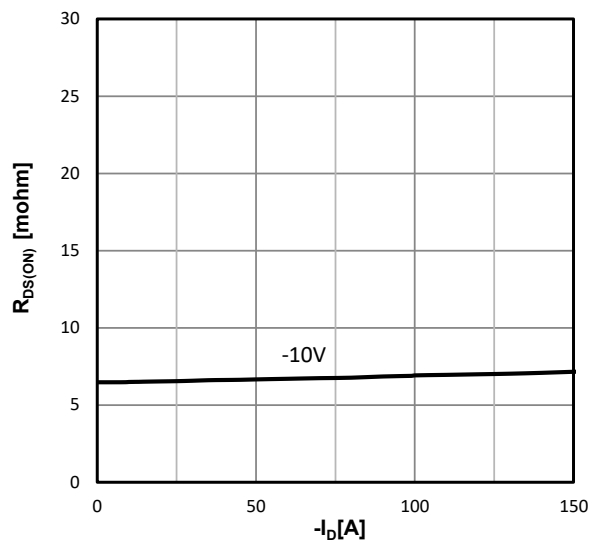
Characteristics Curve:

Figure 1: Typ. output characteristics



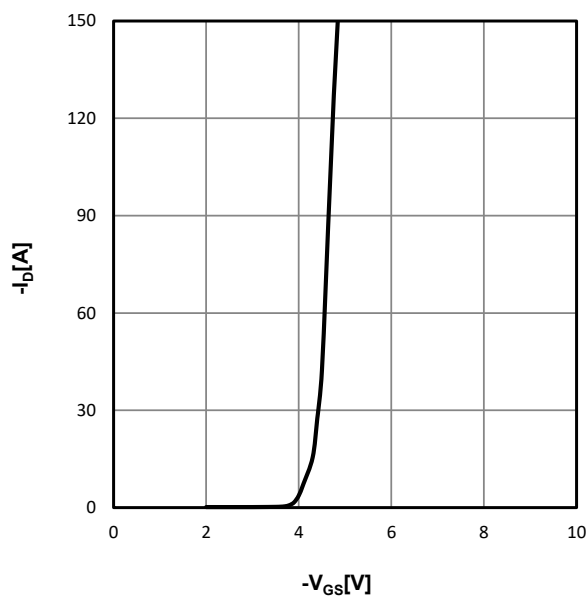
$$I_D = f(V_{DS}), T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$$

Figure 2: Typ. drain-source on resistance



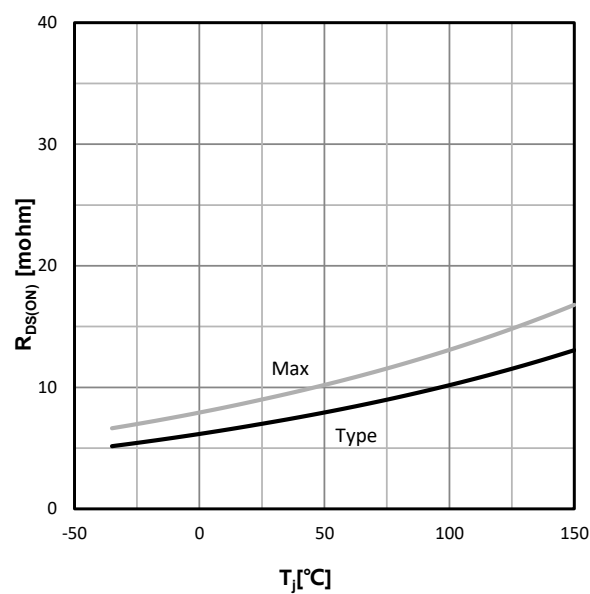
$$R_{DS(on)} = f(I_D), T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$$

Figure 3: Typ. transfer characteristics



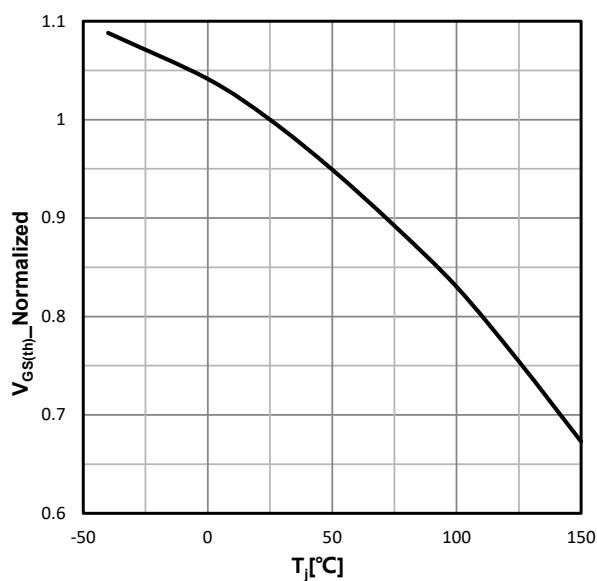
$$I_D = f(V_{GS}), |V_{DS}| > 2|I_D|R_{DS(on)\text{max}};$$

Figure 4: drain-source on resistance



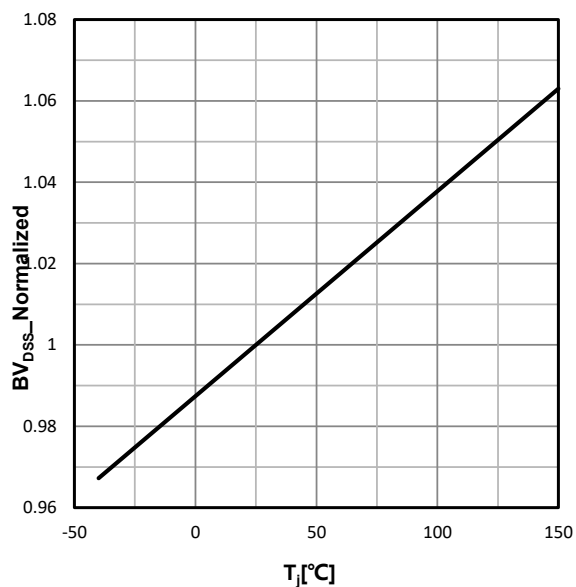
$$R_{DS(on)} = f(T_j), I_D = -20\text{A}, V_{GS} = -10\text{V};$$

Figure 5: Typ. gate threshold voltage



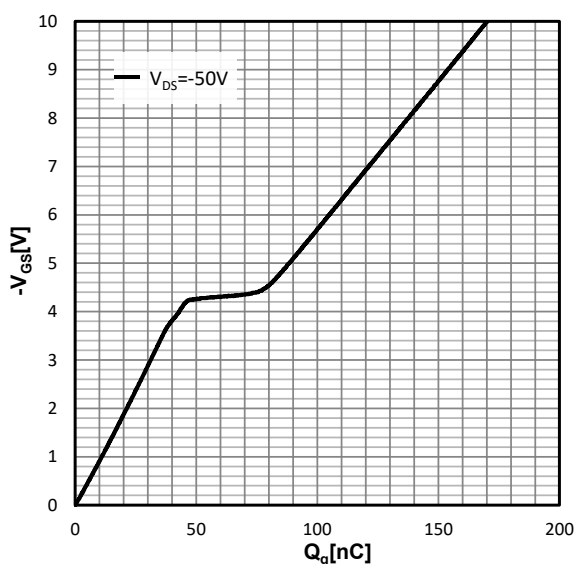
$$V_{GS}=f(T_j), V_{GS}=V_{DS}, I_D=-250\mu A;$$

Figure 6: Drain-source breakdown voltage



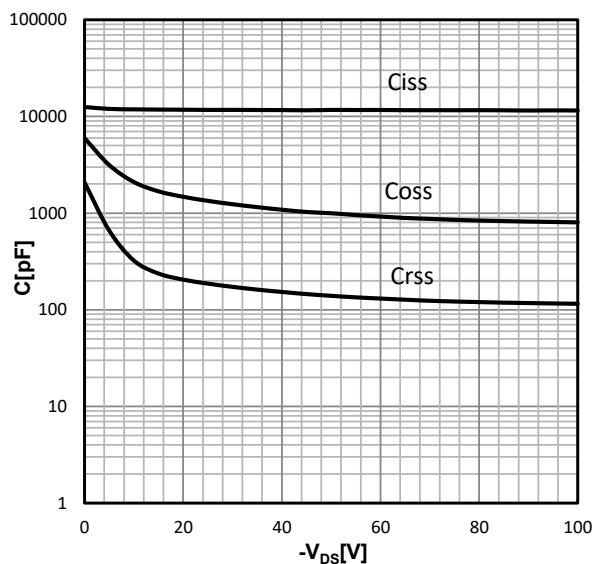
$$V_{BR(DSS)}=f(T_j); I_D=-250\mu A;$$

Figure 7: Typ. gate charge



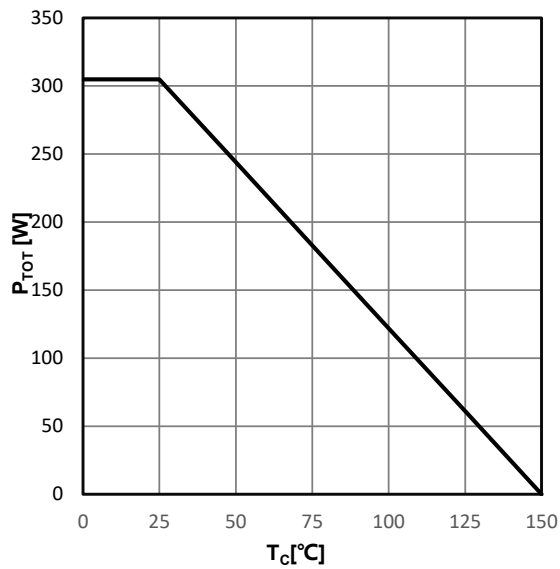
$$V_{GS}=f(Q_g), I_D=-20A, T_j=25^\circ C; \text{parameter: } V_{DS}$$

Figure 8: Typ. Capacitances



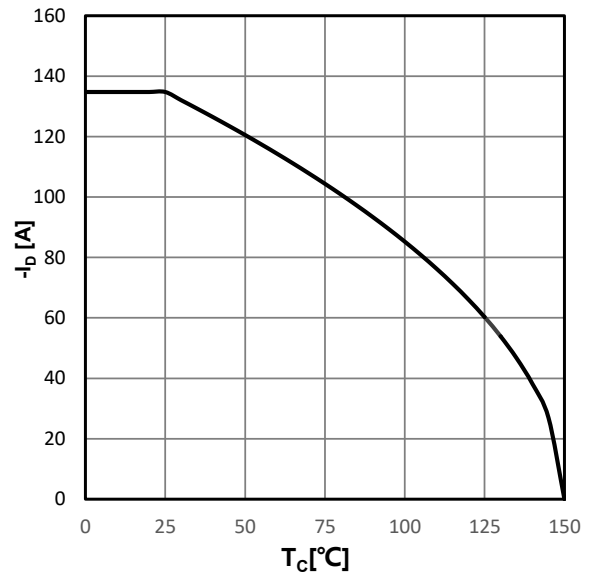
$$C=f(V_{DS}); V_{GS}=0V; f=1.0\text{ MHz};$$

Figure 9: Power dissipation



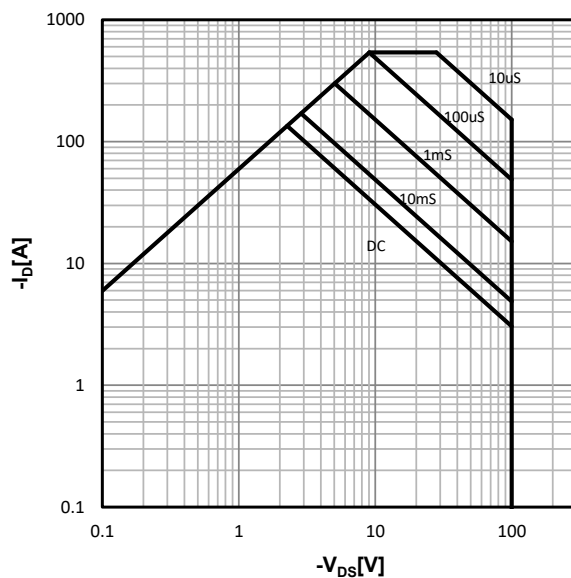
$$P_{\text{tot}} = f(T_c);$$

Figure 10: Drain current



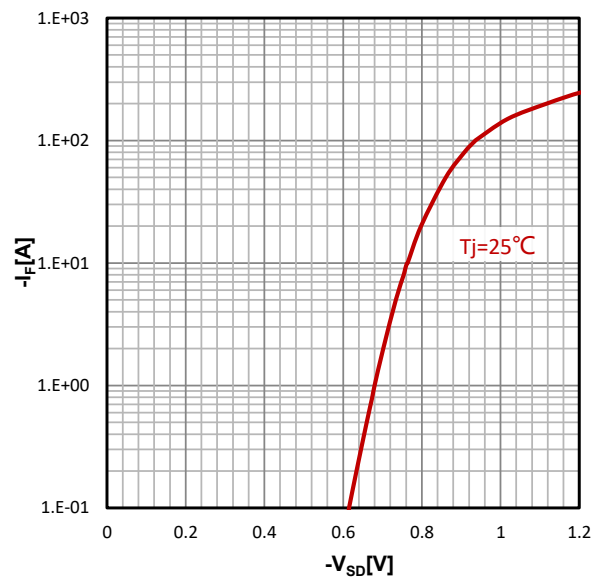
$$I_D = f(T_c);$$

Figure 11: Safe operating area



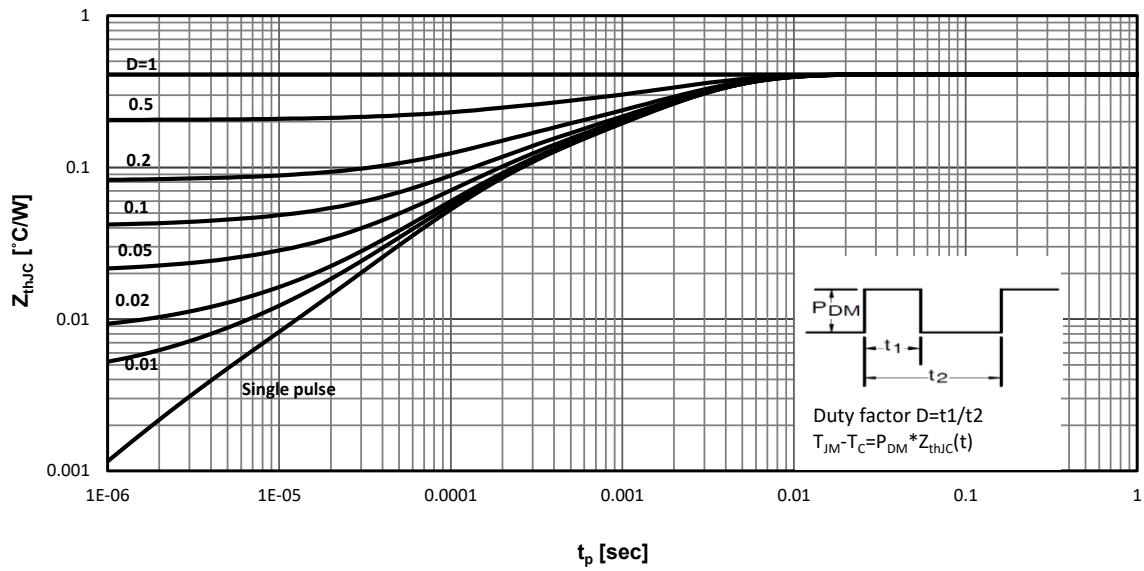
$$I_D = f(V_{\text{DS}}); T_c = 25^{\circ}\text{C}; D = 0; \text{parameter: } t_p$$

Figure 12: Typ. forward characteristics



$$I_F = f(V_{\text{SD}});$$

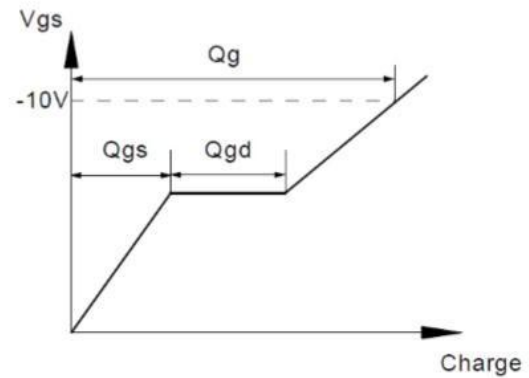
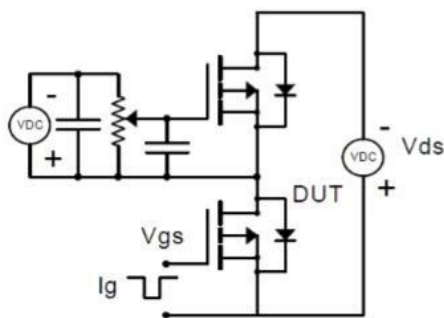
Figure 13: Max. Transient Thermal Impedance



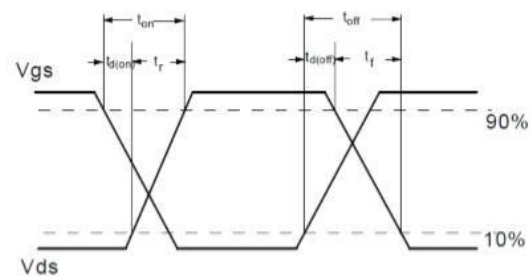
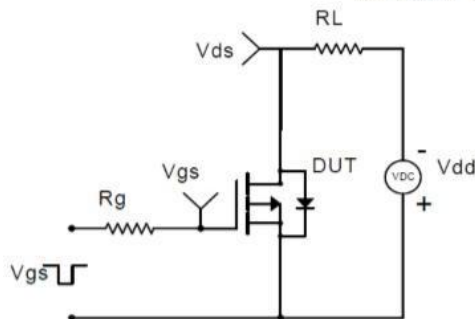
$$Z_{thJC} = f(t_p); \text{ parameter: } D$$

Test Circuit and Waveform:

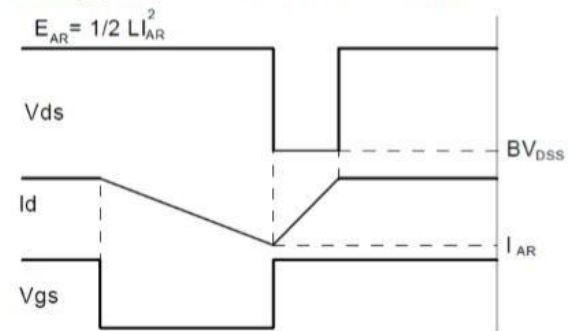
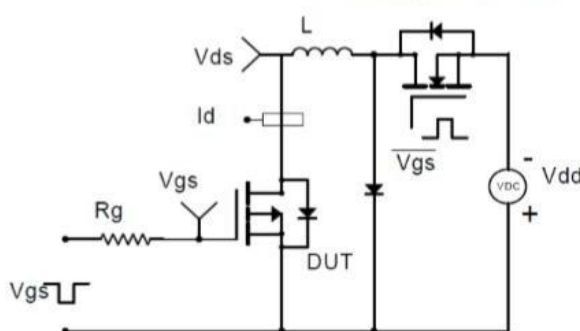
Gate Charge Test Circuit & Waveform



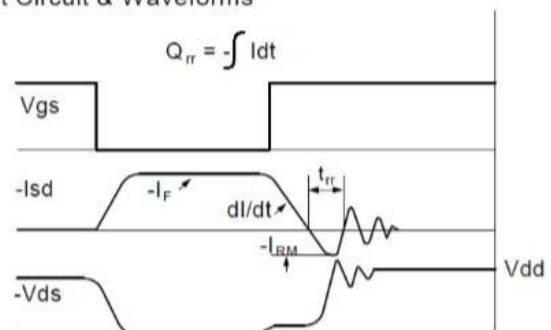
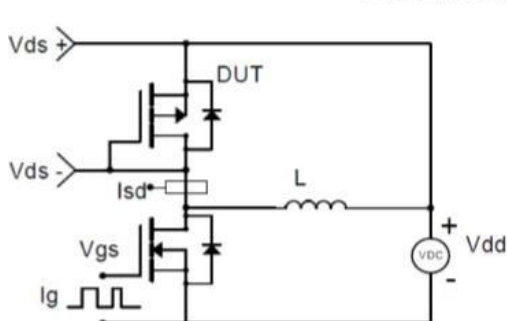
Resistive Switching Test Circuit & Waveforms



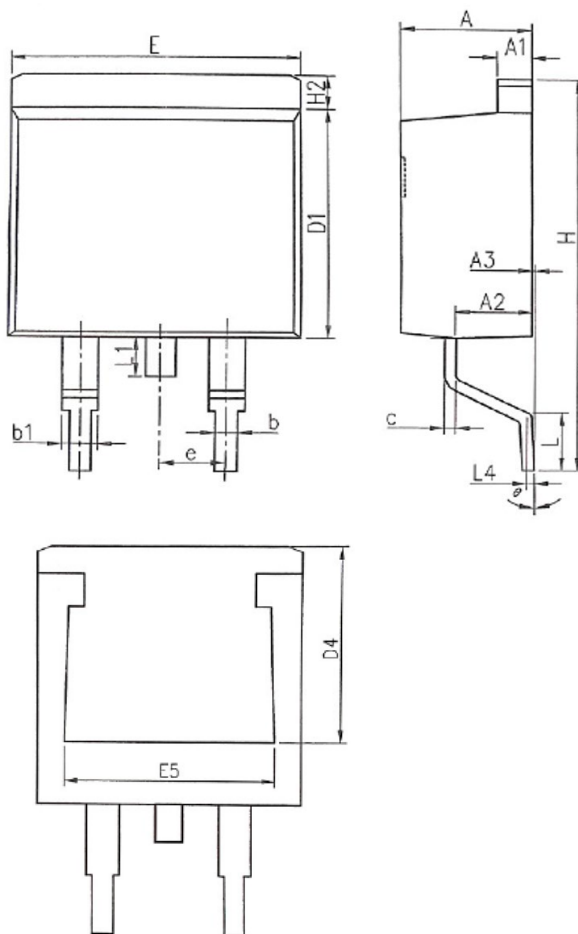
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Mechanical Dimensions for TO-263



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	4.37	4.89
A1	1.17	1.42
A2	2.20	2.90
A3	0.00	0.25
b	0.70	0.96
b1	1.17	1.47
c	0.28	0.60
D1	8.45	9.30
D4	6.60	-
E	9.80	10.40
E5	7.06	-
e	2.54BSC	
H	14.70	15.70
H2	1.07	1.47
L	2.00	2.80
L1	-	1.75
L4	0.254BSC	
θ	0°	9°